an extension of the gate electrode extending outwardly provided above the channel region being formed.--

--26. The thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;

a gate insulating film provided between the channel region and the gate electrode;

a source-drain region connected to said channel region;

a source-drain wiring layer electrically connected to said source-drain region;

a gate wiring layer electrically connected to said gate electrode,

an extension of the channel region extending outwardly therefrom being formed.--

--27. The thin film transistor according to Claim 25 or 26, further comprising extensions extending outwardly from both ends of the gate electrode.--

--28. The thin film transistor according to Claim 25 or 26, further comprising an extension extending outwardly from at least one end of the gate electrode.--

--29. The thin film transistor according to Claim 25 or 26, the gate wiring layer being electrically connected to the extension of the gate electrode by a plurality of contact holes.--

--30. The thin film transistor according to Claim 25 or 26, the gate wiring layer being connected to the gate electrode by at least one contact hole.--

--31. The thin film transistor according to Claim 25 or 26, the source-drain wiring layer being connected to the source-drain region by at least one contact hole.--

--32. The thin film transistor according to Claim 25, an extension of the channel region extending outwardly therefrom being formed.--

--33. A CMOS inverter circuit comprising two of the thin film transistors according to Claim 25 or 26.--

--34. A CMOS inverter circuit comprising two of the thin film transistors according to Claim 25, said thin film transistors having an inverse conductivity type from each other, adjacent source-drain regions of said thin film transistors being connected.--

--35. A display device comprising an active matrix substrate on which a driving circuit including a thin film transistor as defined in Claim 25 or 26 is formed.--

--36. An electronic apparatus comprising a display device as defined in Claim 35.--

--37. The thin film transistor according to Claim 25 or 26, the formed extension extending in a direction substantially perpendicular to the longitudinal direction.--

--38. A display device comprising a CMOS inverter circuit as defined in Claim 33.--

--39. The display device according to Claim 38, the formed extension extending in a direction substantially perpendicular to the longitudinal direction.--

--40. A liquid crystal display device comprising an active matrix substrate on which a driving circuit including a thin film transistor as defined in Claims 25 or 26 being formed.--

--41. An electronic apparatus comprising a liquid crystal display device as defined in Claim 35.--

--42. A liquid crystal display device comprising a CMOS inverter circuit as defined in Claim 33.--

--43. A liquid crystal display device according to Claim 38, the formed extension extending in a direction substantially perpendicular to the longitudinal direction.--

--44. A thin film transistor including a plurality of component parts comprising:

a channel region;

a gate electrode opposed to the channel region;